

Pedram Razavi

List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/10457234/publications.pdf>

Version: 2024-02-01

32
papers

4,010
citations

471509

17
h-index

552781

26
g-index

32
all docs

32
docs citations

32
times ranked

1831
citing authors

#	ARTICLE	IF	CITATIONS
1	Influence of Surface Passivation on Indium Arsenide Nanowire Band Gap Energies. Journal of Electronic Materials, 2019, 48, 6654-6660.	2.2	2
2	Influence of surface stoichiometry and quantum confinement on the electronic structure of small diameter InxGa1-xAs nanowires. Materials Chemistry and Physics, 2018, 206, 35-39.	4.0	2
3	Effect of strain and diameter on electronic and charge transport properties of indium arsenide nanowires. Solid-State Electronics, 2018, 149, 6-14.	1.4	6
4	Electrical performance of III-V gate-all-around nanowire transistors. Applied Physics Letters, 2013, 103, .	3.3	22
5	Influence of channel material properties on performance of nanowire transistors. Journal of Applied Physics, 2012, 111, .	2.5	24
6	Bipolar effects in unipolar junctionless transistors. Applied Physics Letters, 2012, 101, 093507.	3.3	39
7	Emission and absorption of optical phonons in Multigate Silicon Nanowire MOSFETs. Journal of Computational Electronics, 2012, 11, 249-265.	2.5	16
8	Intrinsic gate delay and energy-delay product in junctionless nanowire transistors. , 2012, , .		6
9	Sensitivity analysis of steep subthreshold slope (S-slope) in Junctionless nanotransistors. , 2012, , .		0
10	Electron transport in germanium junctionless nanowire transistors. , 2012, , .		0
11	Mobility enhancement effect in heavily doped junctionless nanowire silicon-on-insulator metal-oxide-semiconductor field-effect transistors. Applied Physics Letters, 2012, 101, 213502.	3.3	45
12	Device Design and Estimated Performance for p-Type Junctionless Transistors on Bulk Germanium Substrates. IEEE Transactions on Electron Devices, 2012, 59, 2308-2313.	3.0	31
13	Influence of discrete dopant on quantum transport in silicon nanowire transistors. Solid-State Electronics, 2012, 70, 92-100.	1.4	15
14	Random dopant variation in junctionless nanowire transistors. , 2011, , .		9
15	Improvement of carrier ballisticity in junctionless nanowire transistors. Applied Physics Letters, 2011, 98, .	3.3	43
16	Characterization of a junctionless diode. Applied Physics Letters, 2011, 99, 013502.	3.3	6
17	Nanowire to Single-Electron Transistor Transition in Trigate SOI MOSFETs. IEEE Transactions on Electron Devices, 2011, 58, 26-32.	3.0	9
18	Influence of Elastic and Inelastic Electron-Phonon Interaction on Quantum Transport in Multigate Silicon Nanowire MOSFETs. IEEE Transactions on Electron Devices, 2011, 58, 1029-1037.	3.0	9

#	ARTICLE	IF	CITATIONS
19	Junctionless Multiple-Gate Transistors for Analog Applications. IEEE Transactions on Electron Devices, 2011, 58, 2511-2519.	3.0	234
20	A Simulation Comparison between Junctionless and Inversion-Mode MuGFETs. ECS Transactions, 2011, 35, 63-72.	0.5	29
21	Junctionless Nanowire Transistor: Complementary Metal-Oxide-Semiconductor Without Junctions. Science of Advanced Materials, 2011, 3, 477-482.	0.7	36
22	Performance estimation of junctionless multigate transistors. Solid-State Electronics, 2010, 54, 97-103.	1.4	487
23	Nanowire transistors without junctions. Nature Nanotechnology, 2010, 5, 225-229.	31.5	1,993
24	Effect of intravalley acoustic phonon scattering on quantum transport in multigate silicon nanowire metal-oxide-semiconductor field-effect transistors. Journal of Applied Physics, 2010, 108, 034510.	2.5	19
25	Reduced electric field in junctionless transistors. Applied Physics Letters, 2010, 96, 073510.	3.3	269
26	Mobility improvement in nanowire junctionless transistors by uniaxial strain. Applied Physics Letters, 2010, 97, .	3.3	38
27	Low subthreshold slope in junctionless multigate transistors. Applied Physics Letters, 2010, 96, .	3.3	195
28	High-Temperature Performance of Silicon Junctionless MOSFETs. IEEE Transactions on Electron Devices, 2010, 57, 620-625.	3.0	359
29	Simulation of Quantum Current Oscillations in Trigate SOI MOSFETs. IEEE Transactions on Electron Devices, 2010, 57, 1102-1109.	3.0	15
30	Nanowire zero-capacitor DRAM transistors with and without junctions. , 2010, , .		17
31	Dissipative transport in Multigate silicon nanowire transistors. , 2010, , .		4
32	A new F(ast)-CMS NEGF algorithm for efficient 3D simulations of switching characteristics enhancement in constricted tunnel barrier silicon nanowire MuGFETs. Journal of Computational Electronics, 2009, 8, 287-306.	2.5	31